

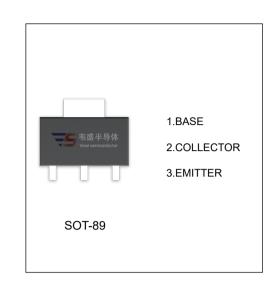
# 2SB1073 TRANSISTOR (PNP)

### **FEATURES**

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- Large peak collector current I<sub>C</sub>

## MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	-30	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-20	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V	
Ic	Collector Current -Continuous	-4	А	
Pc	Collector Power Dissipation	0.5	W	
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	°C	



## **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10μA,I <sub>E</sub> =0	-30			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-20			٧
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA,I <sub>C</sub> =0	-7			٧
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-30V,I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-7V,I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-2A	120		315	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-3A,I <sub>B</sub> =-100mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-6V,I <sub>C</sub> =-50mA,f=200MHz		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-20V,I <sub>E</sub> =0,f=1MHz		40		pF

### **CLASSIFICATION OF hFE**

Rank	Q	R		
Range	120-205	180-315		
Marking	IQ	IR		